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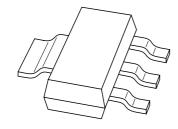
If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS

DATA SHEET



PZT2907APNP switching transistor

Product data sheet Supersedes data of 1997 Jun 02 1999 Apr 14



PNP switching transistor

PZT2907A

FEATURES

- High current (max. 600 mA)
- Low voltage (max. 60 V).

APPLICATIONS

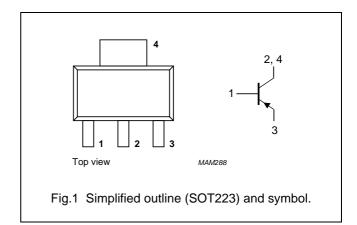
• Switching and linear amplification.

DESCRIPTION

PNP switching transistor in a SOT223 plastic package. NPN complement: PZT2222A.

PINNING

PIN	DESCRIPTION
1	base
2, 4	collector
3	emitter



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	-60	V
V_{CEO}	collector-emitter voltage	open base	_	-60	V
V_{EBO}	emitter-base voltage	open collector	_	-5	V
I _C	collector current (DC)		_	-600	mA
I_{CM}	peak collector current		_	-800	mA
I_{BM}	peak base current		_	-200	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	_	1.15	W
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

PNP switching transistor

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	106	K/W
R _{th j-s}	thermal resistance from junction to soldering point		25	K/W

Note

1. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm². For other mounting conditions, see *"Thermal considerations for SOT223 in the General Part of associated Handbook"*.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

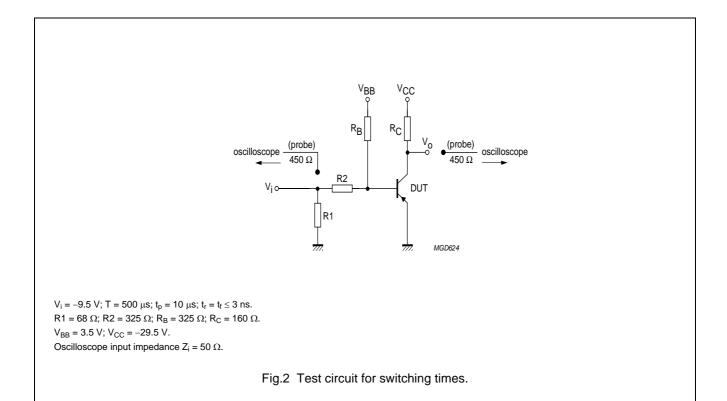
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I _{CBO}	collector cut-off current	I _E = 0; V _{CB} = -50 V	_	-10	nA
		I _E = 0; V _{CB} = -50 V; T _{amb} = 150 °C	Ī-	-10	μА
I _{EBO}	emitter cut-off current	I _C = 0; V _{EB} = -5 V	Ī-	-50	nA
h _{FE}	DC current gain	$I_C = -0.1 \text{ mA}; V_{CE} = -10 \text{ V}$	75	_	
		$I_C = -1 \text{ mA}; V_{CE} = -10 \text{ V}$	100	_	
		$I_C = -10 \text{ mA}; V_{CE} = -10 \text{ V}$	100	_	
		$I_C = -150 \text{ mA}; V_{CE} = -10 \text{ V}; \text{ note 1}$	100	300	
		$I_C = -500 \text{ mA}; V_{CE} = -10 \text{ V}; \text{ note 1}$	50	_	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -150 \text{ mA}$; $I_B = -15 \text{ mA}$; note 1	Ī-	-400	mV
		$I_C = -500 \text{ mA}$; $I_B = -50 \text{ mA}$; note 1	-	-1.6	V
V _{BEsat}	base-emitter saturation voltage	$I_C = -150 \text{ mA}$; $I_B = -15 \text{ mA}$; note 1	_	-1.3	V
		$I_C = -500 \text{ mA}$; $I_B = -50 \text{ mA}$; note 1	_	-2.6	V
C _c	collector capacitance	$I_E = i_e = 0$; $V_{CB} = -10 \text{ V}$; $f = 1 \text{ MHz}$	Ī-	8	pF
C _e	emitter capacitance	$I_C = i_c = 0$; $V_{EB} = -2 \text{ V}$; $f = 1 \text{ MHz}$	Ī-	30	pF
f _T	transition frequency	$I_C = -50 \text{ mA}; V_{CE} = -20 \text{ V};$ f = 100 MHz; note 1	200	_	MHz
Switching t	imes (between 10% and 90% levels)	; (see Fig.2)			
t _{on}	turn-on time	$I_{Con} = -150 \text{ mA}; I_{Bon} = -15 \text{ mA};$	_	40	ns
t _d	delay time	I _{Boff} = 15 mA	_	12	ns
t _r	rise time		_	30	ns
t _{off}	turn-off time		_	365	ns
t _s	storage time		_	300	ns
t _f	fall time		_	65	ns

Note

1. Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

PNP switching transistor

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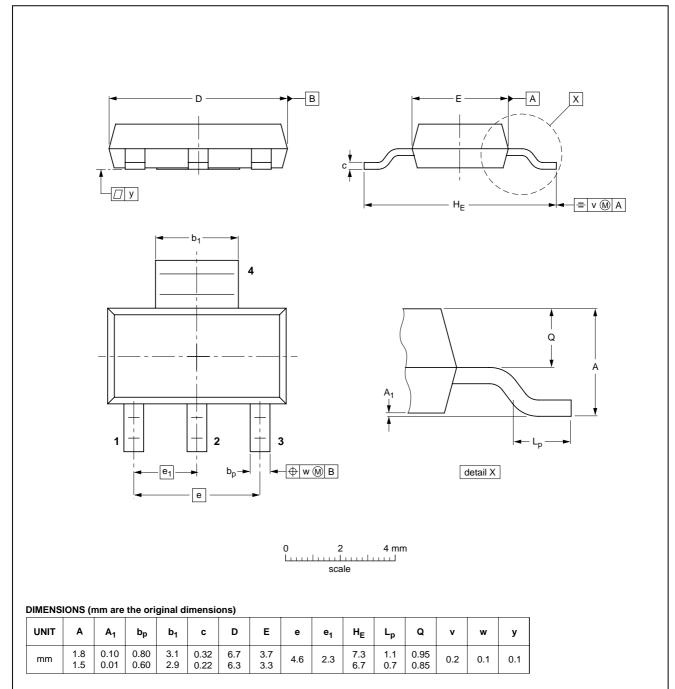
PNP switching transistor

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PACKAGE OUTLINE

Plastic surface mounted package; collector pad for good heat transfer; 4 leads

SOT223



OUTLINE	OUTLINE REFERENCES				EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE	
SOT223			SC-73			-97-02-28 99-09-13	

PNP switching transistor

PZT2907A

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

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